
2SC1213, 2SC1213A

Silicon NPN Epitaxial

HITACHI

Application

- Σ Low frequency amplifier
- Σ Complementary pair with 2SA673 and 2SA673A

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SC1213	2SC1213A	Unit
Collector to base voltage	V_{CBO}	35	50	V
Collector to emitter voltage	V_{CEO}	35	50	V
Emitter to base voltage	V_{EBO}	4	4	V
Collector current	I_C	500	500	mA
Collector power dissipation	P_C	400	400	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

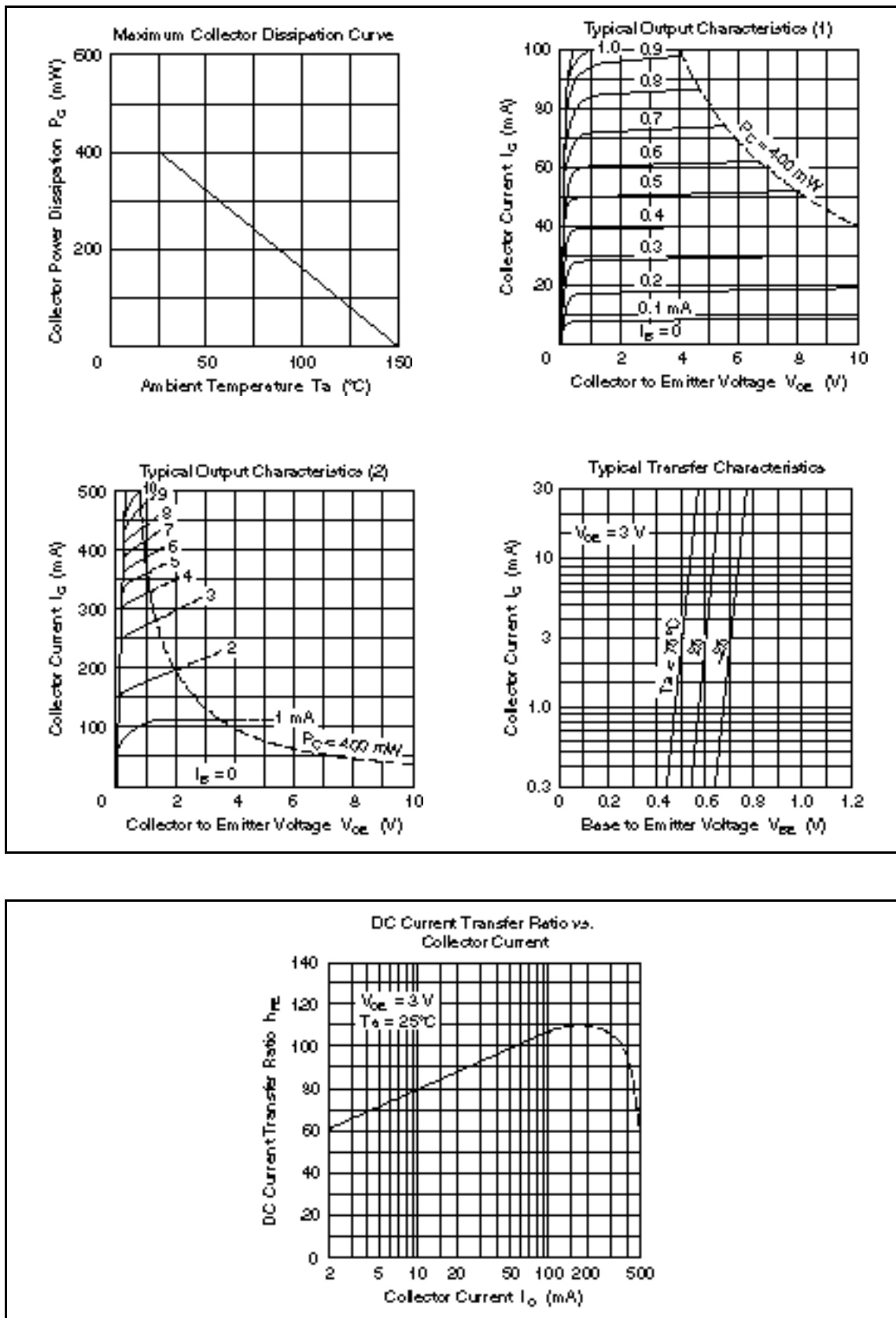
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SC1213			2SC1213A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	35	—	—	50	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	35	—	—	50	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \bullet$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	—	—	4	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	—	—	0.5	μA	$V_{CB} = 20 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE}^{*1}	60	—	320	60	—	320		$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$
	h_{FE}	10	—	—	10	—	—		$V_{CE} = 3 \text{ V}, I_C = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.2	0.6	—	0.2	0.6	V	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	—	0.64	—	—	0.64	—	V	$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$

Notes: 1. The 2SC1213 and 2SC1213A are grouped by h_{FE} as follows.

2. Pulse test

B	C	D
60 to 120	100 to 200	160 to 320



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